Amendment to the claims:

Claims 1-44 (Canceled).

45. (Previously added): An apparatus for delivering media to a wafer, comprising:

a housing defining a process chamber;

a media delivery member coupled to the process chamber;

a spin chuck positioned in the process chamber, the spin chuck having a wafer support surface, wherein the wafer support surface is formed with silicon oxide coated contact points [covered with a coating layer, the coating layer being in a solid state and substantially free of voids]; and

a vacuum supply line coupled to the spin chuck.

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46. (Previously added): The apparatus of claim 45, wherein the coating layer is a dielectric coating layer.

47. (Previously added): The apparatus of claim 45, wherein the coating layer has a composition including a substance from the chemical family SiO_xCH_y , with x ranging from 1-2, inclusive, and y ranging from 0-3, inclusive.

48. (Canceled)

49. (Currently amended): The apparatus of claim 45, wherein the coating layer material has a mechanical hardness equal to $hardness_{coating\ layer}$ and the wafer material has a mechanical hardness equal to $hardness_{wafer}$, and wherein $hardness_{coating\ layer}$ is less than $hardness_{wafer}$. [a corresponding mechanical hardness of the wafer.]

50. (Currently amended): The apparatus of claim 45, wherein the coating layer material has a mechanical hardness equal to $hardness_{coating\ layer}$, and silicon has a mechanical hardness equal to $hardness_{silicon}$, and wherein $hardness_{coating\ layer}$ is less than $hardness_{silicon}$.[a mechanical hardness of silicon.]

51. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 10-100 micrometers.

52. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 1-10 micrometers.

53. (Previously added): The apparatus of claim 45, wherein the coating layer has a thickness in the range of 0.05-1 micrometers.

54. (Previously added): The apparatus of claim 45, wherein the coating material on the wafer support surface has a thickness of 10-100 microns.

55. (Previously added): The apparatus of claim 45, wherein the wafer support surface has a surface area no larger than a surface area of a wafer configured to be positioned on the wafer support surface.

56. (Previously added): The apparatus of claim 45, wherein the wafer support surface includes a plurality of support structures.

57. (Canceled).

58. (Previously added): The apparatus of claim 45, wherein the wafer support surface includes a vacuum ring.

59. (Previously added): The apparatus of claim 59, wherein the vacuum ring is a line contact vacuum ring.

60. (Previously added): An apparatus of claim 45, further comprising a skirt positioned at a periphery and in a non-planar relationship to the wafer support wafer surface.

61. (Previously added): The apparatus of claim 60, wherein the wafer support surface provides a mechanical support for a wafer and the skirt is positioned to be in a non-mechanical supporting position relative to the wafer.

62. (Previously added): The apparatus of claim 60, wherein the skirt is sized to permit a wafer positioned on the wafer support surface to extend beyond a periphery of the skirt.

63. (Previously added): The apparatus of claim 60, wherein the skirt and wafer support surface are sized to be at least equal to a size of a wafer positioned on the wafer support surface.

64. (Previously added): The apparatus of claim 45, further comprising at least one wafer transporter coupled to the process chamber.